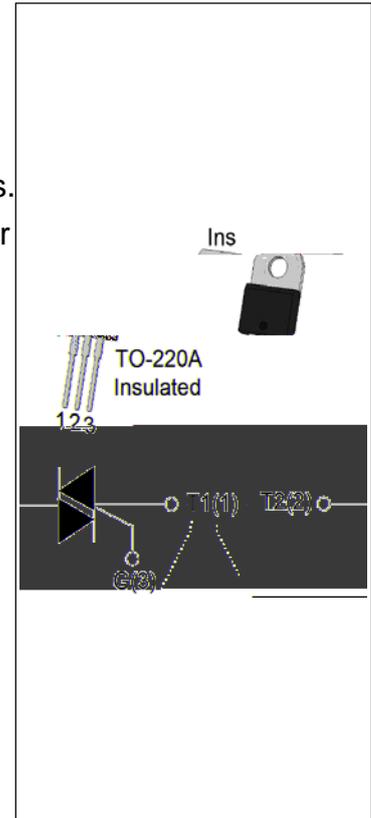




JST10A-800CW 10A TRIAC

Rev.A.1.0

The JST10A-800CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST10A-800CW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, JST10A-800CW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.



| Symbol | Value | Unit |
|-------------------|----------|------|
| $I_{T(RMS)}$ | 10 | A |
| V_{DRM}/V_{RRM} | 800 | V |
| $I_{GT} / /$ | 35/35/35 | mA |

| Parameter | Symbol | Value | Unit |
|--|--------------|---------|-----------|
| Storage junction temperature range | T_{stg} | -40-150 | |
| Operating junction temperature range | T_j | -40-125 | |
| Repetitive peak off-state voltage ($T_j=25^\circ C$) | V_{DRM} | 800 | V |
| Repetitive peak reverse voltage ($T_j=25^\circ C$) | V_{RRM} | 800 | V |
| RMS on-state current ($T_c = 93^\circ C$) | $I_{T(RMS)}$ | 10 | A |
| Non repetitive surge peak on-state current (full cycle, $t_p=20ms$, $T_j=25^\circ C$) | I_{TSM} | 100 | A |
| Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$, $T_j=25^\circ C$) | | 110 | |
| I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$) | I^2t | 50 | A^2s |
| Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100Hz$, $T_j=125^\circ C$) | di/dt | 100 | $A/\mu s$ |
| Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$) | I_{GM} | 4 | A |
| Average gate power dissipation ($T_j=125^\circ C$) | $P_{G(AV)}$ | 0.5 | W |

| | | | |
|--|----------|----|----|
| Peak gate power | P_{GM} | 10 | W |
| Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7) | V_{pp} | 4 | kV |

($T_j=25$ unless otherwise specified)

| Symbol | Test Condition | Quadrant | Value | | Unit |
|-----------|---|----------|-------|-----|------------|
| I_{GT} | $V_D=12V R_L=33\Omega$ | - - | MAX. | 35 | mA |
| V_{GT} | | - - | MAX. | 1 | V |
| V_{GD} | $V_D=V_{DRM} T_j=125$ $R_L=3.3K\Omega$ | - - | MIN. | 0.2 | V |
| I_L | $I_G=1.2I_{GT}$ | - | MAX. | 50 | mA |
| | | | | 60 | |
| I_H | $I_T=500mA$ | | MAX. | 40 | mA |
| dV/dt | $V_D=540V$ Gate Open $T_j=125$ | | MIN. | 700 | V/ μs |
| (dI/dt)c | (dV/dt)c=20V/ μs $T_j=125$ | | MIN. | 10 | A/ms |
| t_{on} | $I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$ | | TYP. | 3 | μs |
| t_{off} | | | | 30 | |

| Symbol | Parameter | | Value(MAX.) | Unit |
|-----------|---------------------------|-----------|-------------|------------|
| V_{TM} | $I_{TM}=16A t_p=380\mu s$ | $T_j=25$ | 1.5 | V |
| V_{TO} | Threshold voltage | $T_j=125$ | 0.77 | V |
| R_D | Dynamic resistance | $T_j=125$ | 35 | m Ω |
| I_{DRM} | $V_D=V_{DRM} V_R=V_{RRM}$ | $T_j=25$ | 5 | μA |
| I_{RRM} | | $T_j=125$ | 0.4 | mA |

| Symbol | Parameter | Value | Unit |
|---------------|--------------------------|-------|-------------|
| $R_{th(j-c)}$ | junction to case (AC) | 2.3 | /W |
| $R_{th(j-a)}$ | junction to ambient (AC) | 60 | /W |

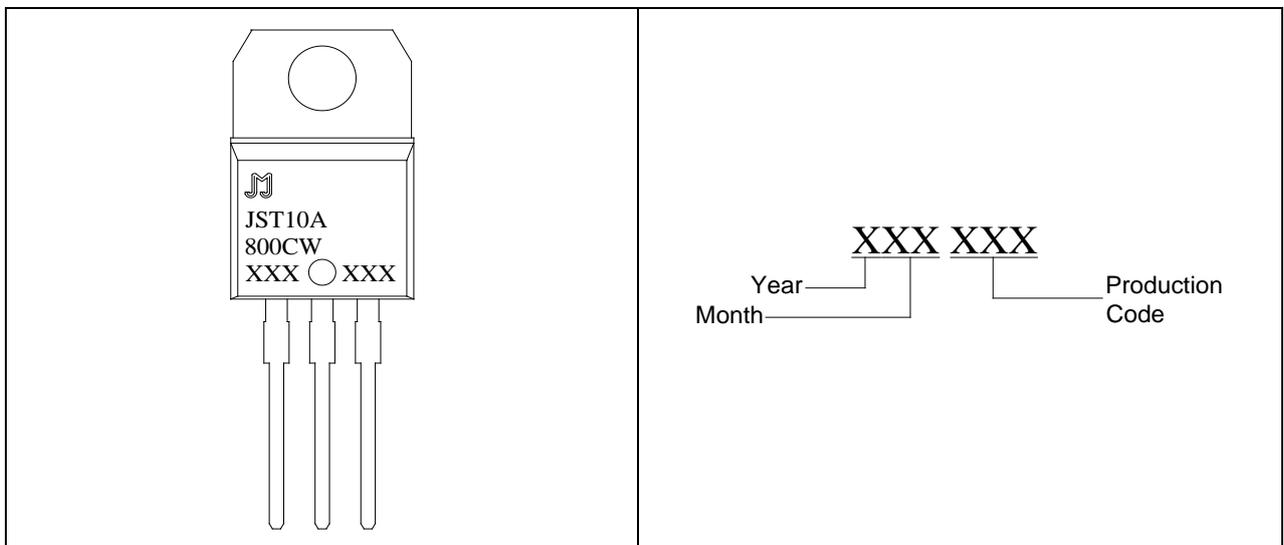
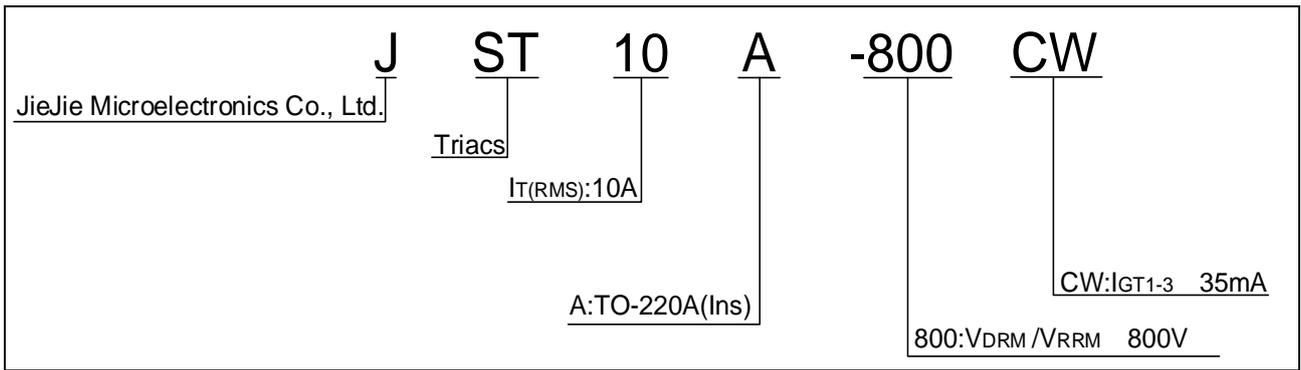


FIG.1 Maximum power dissipation versus RMS on-state current

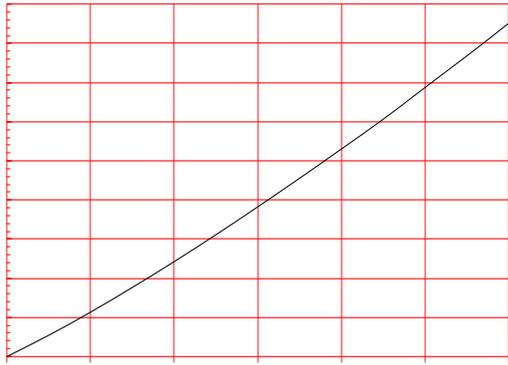


FIG.2: RMS on-state current versus case temperature

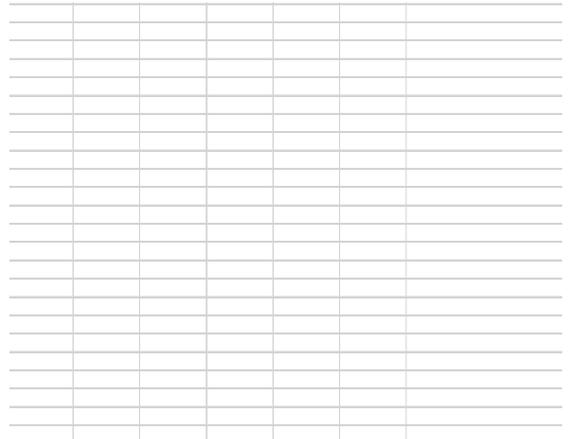
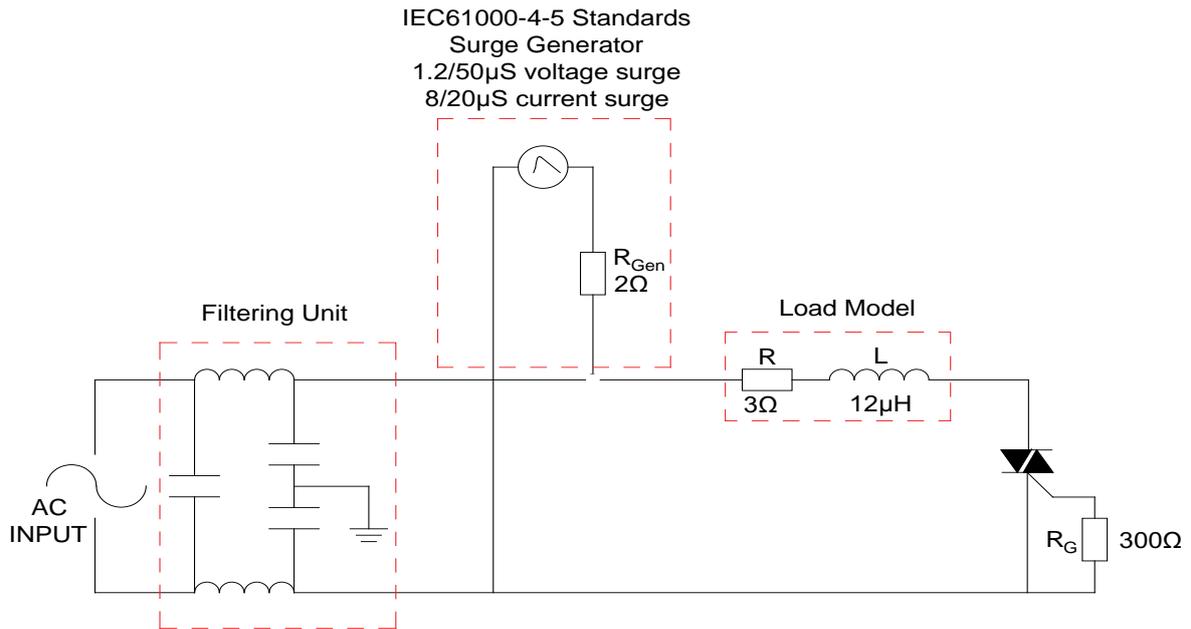


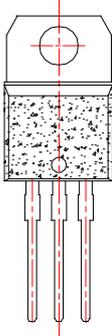
FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



| Order code | Voltage V_{DRM}/V_{RRM} (V) | IGT(mA) | Package | Base qty. (pcs) | Delivery mode |
|--------------|----------------------------------|---------|--------------|--------------------|------------------|
| | | - - | | | |
| JST10A-800CW | 800 | 35 | TO-220A(Ins) | 50 | Tube |

Document Revision History

| Date | Revision | Changes |
|--------------|----------|--------------|
| Apr.11, 2023 | A.1.0 | Last updated |



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